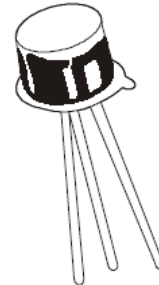


Small Signal General Purpose Transistor (PNP)

Features

- Switching and Linear Application
DC to VHF Amplifier Application
- RoHS Compliant



Mechanical Data

Case:	TO-18, Metal can package
Terminals:	Solderable per MIL-STD-202, Method 208
Weight:	0.35 grams

TO-18



Maximum Ratings *(T_{Ambient}=25°C unless noted otherwise)*

Symbol	Description	2N2907A	Unit
V_{CB0}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EB0}	Emitter-Base Voltage	5.0	V
I_C	Collector Current Continuous	600	mA
P_D	Power Dissipation at T _A =25°C	400	mW
	Power Dissipation Derate above T _A =25°C	2.28	mW/°C
	Power Dissipation at T _C =25°C	1.8	W
	Power Dissipation Derate above T _C =25°C	10.3	mW/°C
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-65 to +200	°C

Small Signal General Purpose Transistor (PNP)

2N2907A

Electrical Characteristics ($T_{Ambient}=25^{\circ}C$ unless noted otherwise)

Symbol	Description	Min.	Max.	Unit	Conditions
VCBO	Collector-Base Voltage	60	-	V	$I_C=10\mu A, I_E=0$
*VCEO	Collector-Emitter Voltage	60	-	V	$I_C=10mA, I_B=0$
VEBO	Emitter-Base Voltage	5.0	-	V	$I_E=10\mu A, I_C=0$
hFE	D.C. Current Gain	75	-		$V_{CE}=10V, I_C=0.1mA$
		100	-		$V_{CE}=10V, I_C=1mA$
		100	-		$V_{CE}=10V, I_C=10mA$
		100	300		$*V_{CE}=10V, I_C=150mA$
		50	-		$*V_{CE}=10V, I_C=500mA$
*VCE(sat)	Collector-Emitter Saturation Voltage	-	0.4	V	$I_C=150mA, I_B=15mA$
		-	1.6	V	$I_C=500mA, I_B=50mA$
*VBE(sat)	Base-Emitter Saturation Voltage	-	1.3	V	$I_C=150mA, I_B=15mA$
		-	2.6	V	$I_C=500mA, I_B=50mA$
ICBO	Collector-Cut-off Current	-	10	nA	$V_{CB}=50V, I_E=0$
		-	10	μA	$V_{CB}=50V, I_E=0, T_A=150^{\circ}C$
ICEX	Collector-Cut-off Current	-	50	nA	$V_{CE}=30V, V_{BE}=0.5V$
IB	Base Current	-	50	nA	$V_{CE}=30V, V_{BE}=0.5V$
**ft	Transition Frequency	200	-	MHz	$I_C=50mA, V_{CE}=20V, f=100MHz$
Cob	Out-Put Capacitance	-	8.0	pF	$V_{CB}=10V, I_E=0, f=100KHz$
Cib	In-Put Capacitance	-	30	pF	$V_{BE}=2V, I_C=0, f=100KHz$
td	Delay Time	-	10	nS	$I_C=150mA, I_{B1}=15mA$
tr	Rise Time	-	40	nS	$V_{CC}=30V$
ton	Turn-On Time	-	45	nS	
ts	Storage Time	-	80	nS	$I_C=150mA, I_{B1}=I_{B2}=15mA$
tf	Fall Time	-	30	nS	$V_{CC}=6V$
toff	Turn-Off Time	-	100	nS	

*Pulse Test: -Pulse Width=300 μ s, Duty Cycle=2%

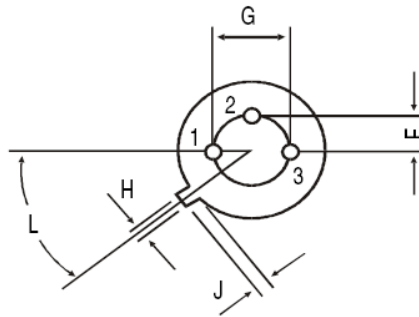
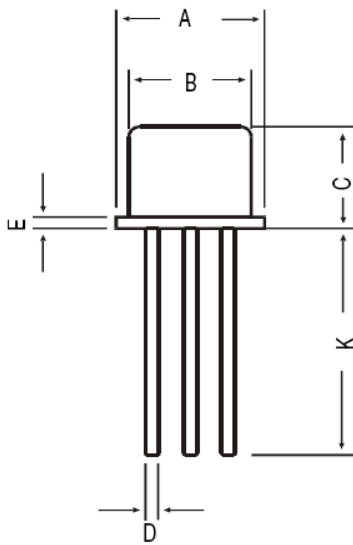
Small Signal General Purpose Transistor (PNP)

2N2907A

**ft is defined as the frequency at which h_{fe} extrapolates to unity

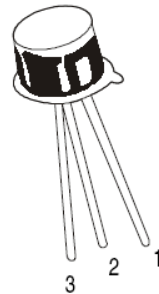
Dimensions in mm

TO-18



All dimensions in mm.

DIM	MIN	MAX
A	5.24	5.84
B	4.52	4.97
C	4.31	5.33
D	0.40	0.53
E	—	0.76
F	—	1.27
G	—	2.97
H	0.91	1.17
J	0.71	1.21
K	12.70	—
L	45 DEG	



PIN CONFIGURATION

1. EMITTER
2. BASE
3. COLLECTOR

Packing Information:

Standard Pack	
Details	Net Weight/Qty.
1k/polybag	350gm/1k pcs

Small Signal General Purpose Transistor (PNP)

2N2907A

Carton Information:

Inner Carton Box	
Size	Qty.
3' x 7.5' x 7.5'	5k pcs

Outer Carton Box		
Size	Qty.	Gross Weight
17' x 15' x 13.5'	80k pcs	34kgs

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